TOSHIBA Field Effect Transistor Silicon N-Channel MOS Type (π-MOS VII)

2SK3669

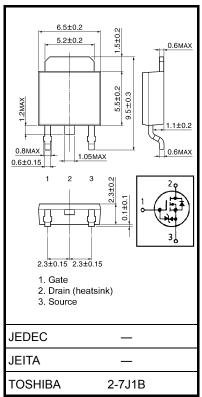
Switching Regulator, Audio Amplifier and Motor Drive Applications

- Low drain-source ON-resistance: $R_{DS (ON)}$ = 95 m Ω (typ.)
- High forward transfer admittance: $|Y_{fs}| = 6 S (typ.)$
- Low leakage current: I_{DSS} = 100 μ A (max) (V_{DS} = 100 V)

Enhancement mode : V_{th} = 3.0 to 5.0 V (V_{DS} = 10 V, I_D = 1 mA)

Absolute Maximum Ratings (Ta = 25°C)

Characteristic		Symbol	Rating	Unit	
Drain-source voltage		V _{DSS}	100	V	
Drain-gate voltage ($R_{GS} = 20 \text{ k}\Omega$)		V _{DGR}	100	V	
Gate-source voltage		V _{GSS}	±20	V	
Drain current	DC (Note 1)	ID	10		
	Pulse (t _w ≤ 10 ms) (Note 1)	I _{DP}	15	А	
	Pulse (t _w ≤ 1 ms) (Note 1)	IDP	28		
Drain power dissipation (Tc = 25° C)		PD	20	W	
Single-pulse avalanche energy (Note 2)		E _{AS}	280	mJ	
Avalanche current		I _{AR}	10	А	
Repetitive avalanche energy (Note 3)		E _{AR}	2	mJ	
Channel temperature		T _{ch}	150	°C	
Storage temperature range		T _{stg}	–55 to 150	°C	



Weight: 0.36 g (typ.)

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Thermal Characteristics

Characteristics	Symbol	Мах	Unit	
Thermal resistance, channel to case	R _{th (ch−c)}	6.25	°C/W	
Thermal resistance, channel to ambient	R _{th (ch−a)}	125	°C/W	

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: V_DD = 50 V, T_ch = 25 $^\circ\text{C}$ (initial), L = 3.44 mH, I_AR = 10 A, R_G = 25 Ω

Note 3: Repetitive rating: pulse width limited by maximum channel temperature

This transistor is an electrostatic-sensitive device. Handle with care.

Unit: mm

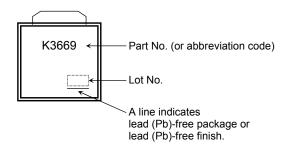
Electrical Characteristics (Ta = 25°C)

Characteristic		Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I _{GSS}	$V_{GS} = \pm 16 \text{ V}, \text{ V}_{DS} = 0 \text{ V}$	_		±100	nA
Drain cutoff current		I _{DSS}	$V_{DS} = 100 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$	_	_	100	μA
Drain-source breakdown voltage		V (BR) DSS	$I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$	100			V
Gate threshold voltage		V _{th}	$V_{DS} = 10 \text{ V}, \text{ I}_{D} = 1 \text{ mA}$	3.0		5.0	V
Drain-source ON-resistance		R _{DS (ON)}	$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 5 \text{ A}$		95	125	mΩ
Forward transfer admittance		Y _{fs}	$V_{DS} = 10 \text{ V}, I_D = 5 \text{ A}$	3	6		S
Input capacitance		C _{iss}	V _{DS} = 10 V, V _{GS} = 0 V, f = 1 MHz		480		pF
Reverse transfer capacitance		C _{rss}			9		
Output capacitance		C _{oss}			220		
	Rise time	tr	V_{GS} 0 V $I_D = 10 \text{ A}$ V _{OUT} 0 V GS $C \in G$ $C \in G$ $C \in G$ $C \in G$ $C \in G$ $C \in G$		2	_	- ns
Switching time	Turn-on time	t _{on}		_	12	_	
	Fall time	t _f			2	_	
	Turn-off time	t _{off}	V _{DD} ≈ 50 V Duty ≤ 1%, t _w = 10 μs	_	12		
Total gate charge (gate-source plus gate-drain)		Qg	V _{DD} ≈ 80 V, V _{GS} = 10 V,		8.0		nC
Gate-source charge		Q _{gs}	$I_{\rm D} = 10 {\rm A}$	_	5.6		
Gate-drain ("Miller") charge		Q _{gd}] [_	2.4	—	

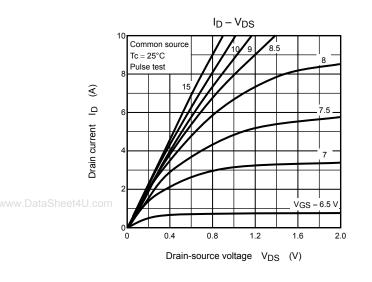
Source-Drain Diode Ratings and Characteristics (Ta = 25°C)

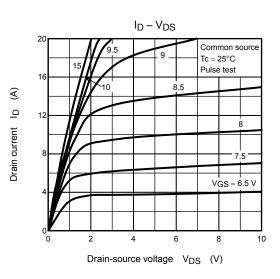
Characteristic	Symbol	Test Condition	Min	Тур.	Мах	Unit
Continuous drain reverse current (Note 1)	I _{DR}	_		_	10	А
Pulse drain reverse current $(t_W \le 10 \text{ ms}) \text{ (Note 1)}$	I _{DRP}	_	_	_	15	А
Pulse drain reverse current $(t_w \le 1 \text{ ms}) \text{ (Note 1)}$	I _{DRP}	—	_	_	28	А
Forward voltage (diode)	V _{DS2F}	I _{DR1} = 10 A, V _{GS} = 0 V	_	_	-1.7	V
Reverse recovery time	t _{rr}	I _{DR} = 10 A, V _{GS} = 0 V,		65	_	ns
Reverse recovery charge	Q _{rr}	dI _{DR} /dt = 50 A/µs	_	90		nC

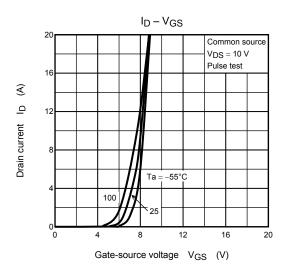
Marking



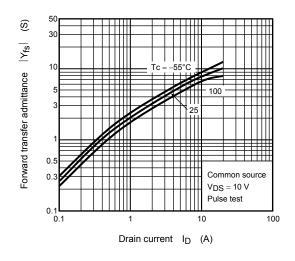
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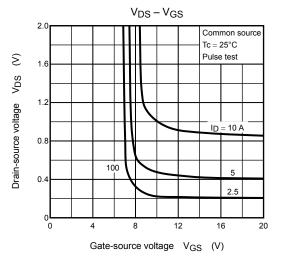




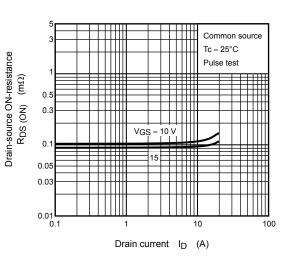




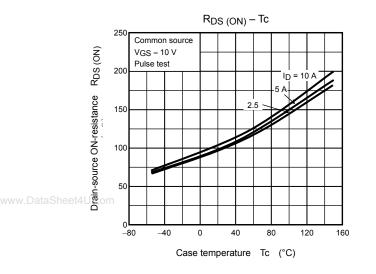


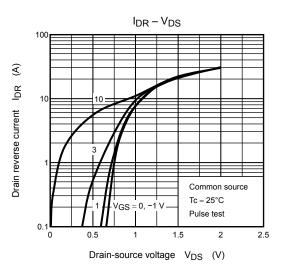


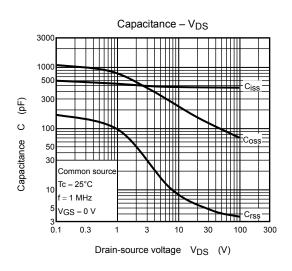


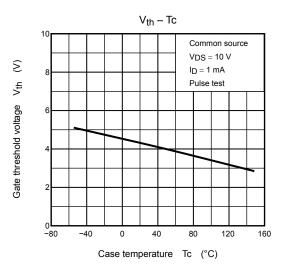


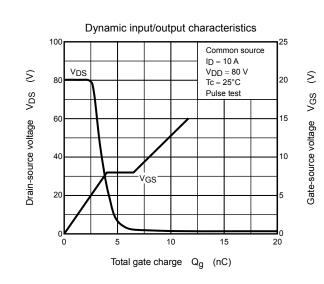
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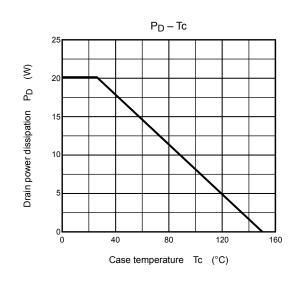






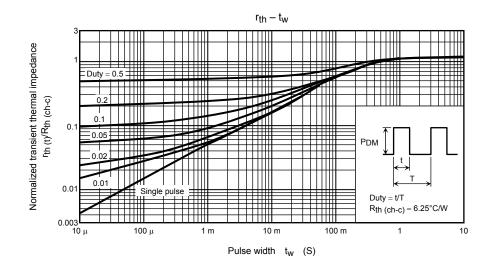




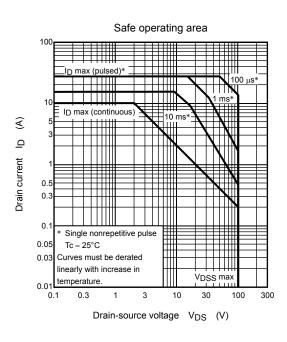


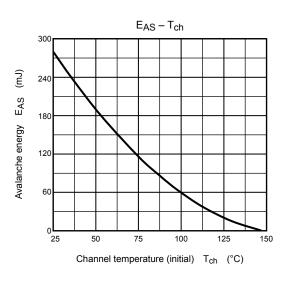
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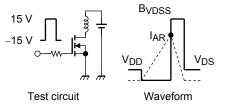
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